



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



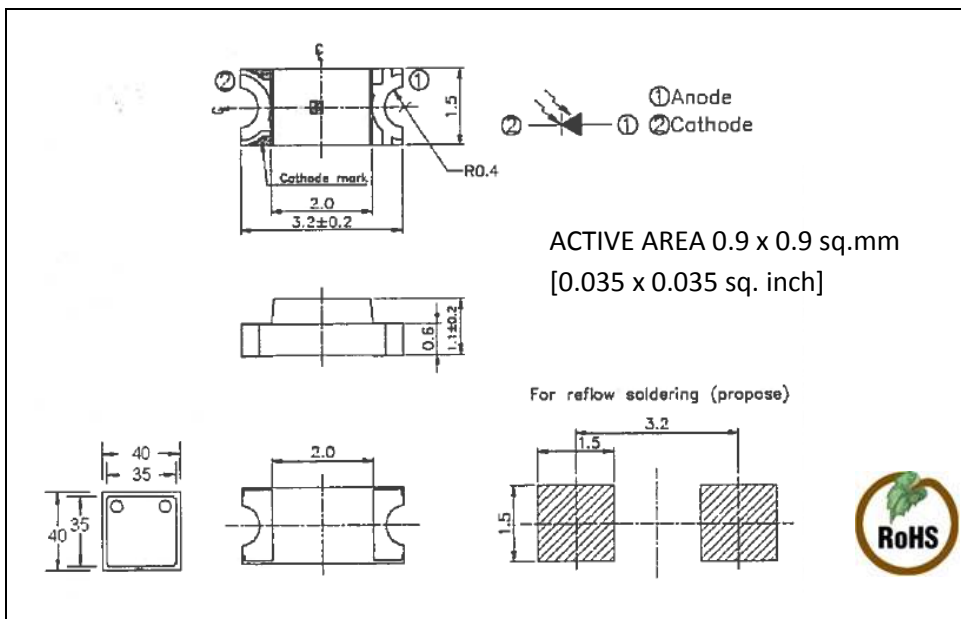
Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





FEATURES

- Small Footprint
- Low Capacitance
- High Speed

DESCRIPTION

The **SD040-101-411** is an UV Enhanced Silicon Photodiode assembled in a 1206 SMT package.

APPLICATIONS

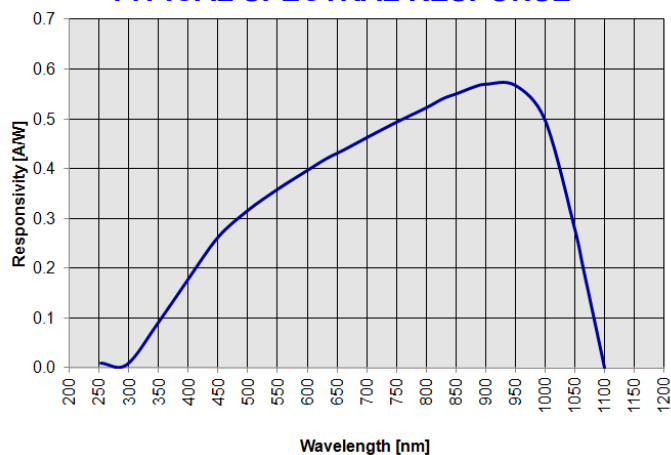
- Industrial Sensors
- Light Management
- Handheld Devices

ABSOLUTE MAXIMUM RATING

$T_a = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V_R	Reverse Voltage		50	V
T_{Op}	Operating Temperature	-40	+105	$^\circ\text{C}$
T_{Stg}	Storage Temperature	-50	+125	$^\circ\text{C}$
T_S	Soldering Temperature		+260	$^\circ\text{C}$

TYPICAL SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING

$T_a = 25^\circ\text{C}$, UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_f	Forward Voltage	$I_f = 10\text{ mA}$	0.5	0.8	1.3	V
I_L	Light Current (2856K)	$V_R = 5\text{V}; H = 1000\text{ lux}$	-	9.0	-	μA
V_{br}	Breakdown Voltage	$I_R = 100\ \mu\text{A}$	50	-	-	V
R_{sh}	Shunt Resistance	$V_{bias} = 10\text{ mV}$	-	1.0	-	$\text{G}\Omega$
I_d	Dark Current	$V_R = 10\text{ V}$	-	-	0.5	nA
C_j	Junction Capacitance	$V_R = 5\text{V}; f = 1000\text{ kHz}$	-	20	-	pF

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. © 2014 Advanced Photonix, Inc. All rights reserved.

Advanced Photonix Inc. 1240 Avenida Acaso, Camarillo CA 93012 • Phone (805) 987-0146 • Fax (805) 484-9935 • www.advancedphotonix.com